Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0200
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0300
I_D (A)	12
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified [d]
- 100 % R_g and UIS tested
- Material categorization:
  For definitions of compliance please see www.vishay.com/doc?99912

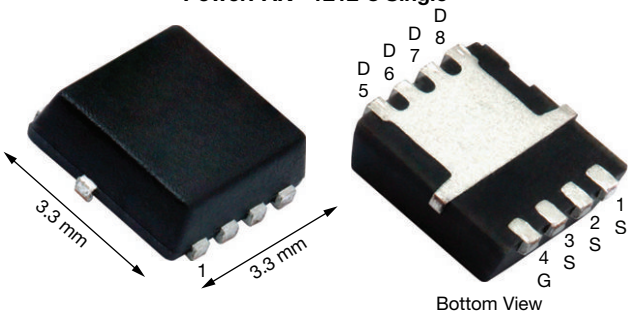
AUTOMOTIVE GRADE

Pb-free

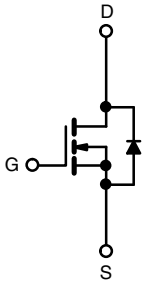
RoHS COMPLIANT

HALOGEN FREE

PowerPAK® 1212-8 Single



Bottom View



N-Channel MOSFET

Marking Code: Q018

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and Halogen-free	SQS840EN-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current [a]	T_C = 25 °C	I_D	12	A
	T_C = 125 °C		12	
Continuous Source Current (Diode Conduction) [a]		I_S	12	
Pulsed Drain Current [b]		I_{DM}	48	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	19	
Single Pulse Avalanche Energy		E_{AS}	18	mJ
Maximum Power Dissipation [b]	T_C = 25 °C	P_D	33	W
	T_C = 125 °C		11	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	°C
Soldering Recommendations (Peak Temperature) [e, f]			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount [c]	R_{thJA}	81	°C/W
Junction-to-Case (Drain)		R_{thJC}	4.5	

Notes

a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR4 material).
d. Parametric verification ongoing.
e. See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

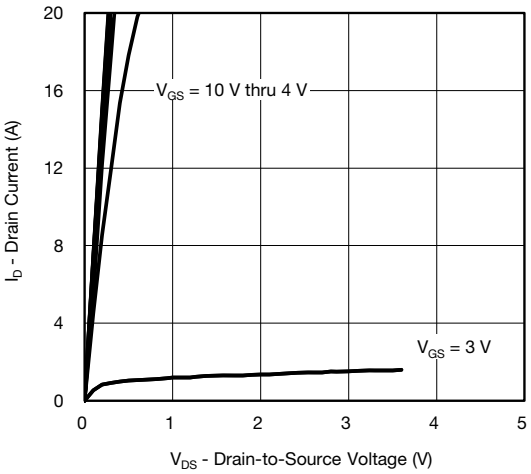
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		40	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		1.5	2.0	2.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 40 V	-	-	1	µA
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 125 °C	-	-	50	
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 175 °C	-	-	150	
On-State Drain Current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ³ 5 V	20	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 7.5 A	-	0.0138	0.0200	Ω
		V_{GS} = 10 V	I_D = 7.5 A, T_J = 125 °C	-	-	0.0280	
		V_{GS} = 10 V	I_D = 7.5 A, T_J = 175 °C	-	-	0.0340	
		V_{GS} = 4.5 V	I_D = 6.5 A	-	0.0183	0.0300	
Forward Transconductance [b]	g_{fs}	V_{DS} = 15 V, I_D = 7.5 A		-	31	-	S
Dynamic [b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 20 V, f = 1 MHz	-	825	1031	pF
Output Capacitance	C_{oss}			-	131	164	
Reverse Transfer Capacitance	C_{rss}			-	58	73	
Total Gate Charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 20 V, I_D = 16.4 A	-	15	22.5	nC
Gate-Source Charge [c]	Q_{gs}			-	2.8	-	
Gate-Drain Charge [c]	Q_{gd}			-	2.9	-	
Gate Resistance	R_g	f = 1 MHz		1.6	3.28	5	Ω
Turn-On Delay Time [c]	$t_{d(on)}$	V_{DD} = 20 V, R_L = 20 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		-	7.6	11.4	ns
Rise Time [c]	t_r			-	9.4	14.1	
Turn-Off Delay Time [c]	$t_{d(off)}$			-	21.6	32.4	
Fall Time [c]	t_f			-	6.4	9.6	
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed Current [a]	I_{SM}			-	-	48	A
Forward Voltage	V_{SD}	I_F = 4.8 A, V_{GS} = 0 V		-	0.8	1.2	V

Notes

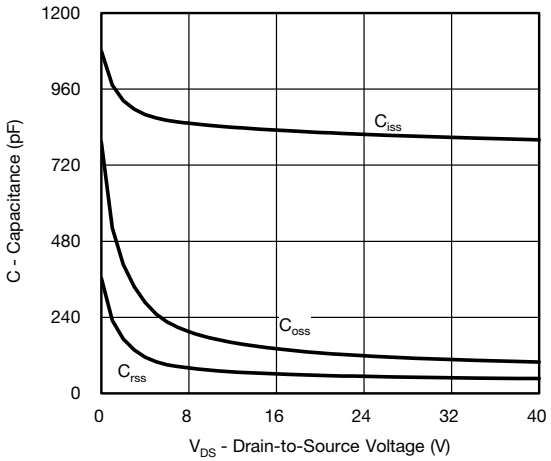
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

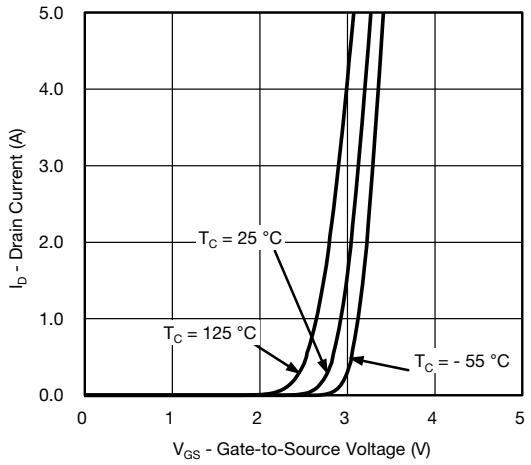
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



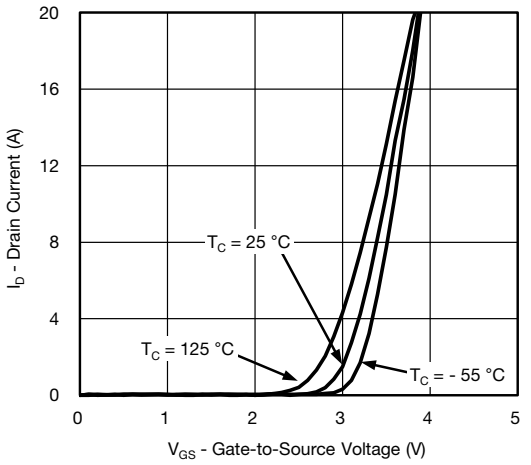
Output Characteristics



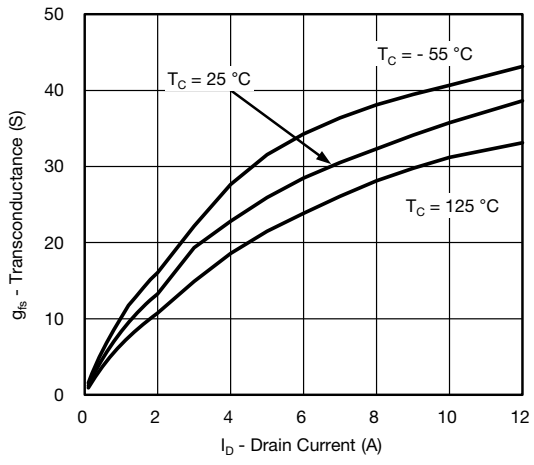
Capacitance



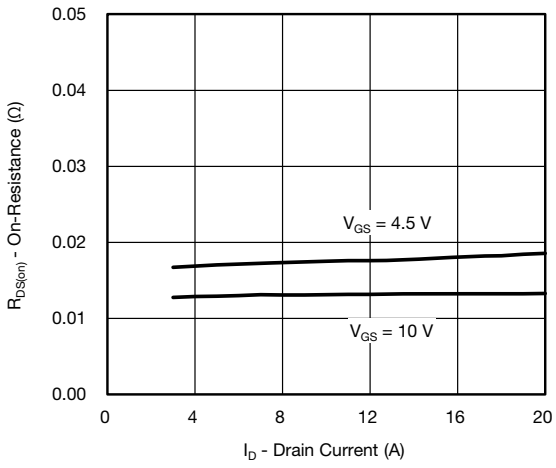
Transfer Characteristics



Transfer Characteristics

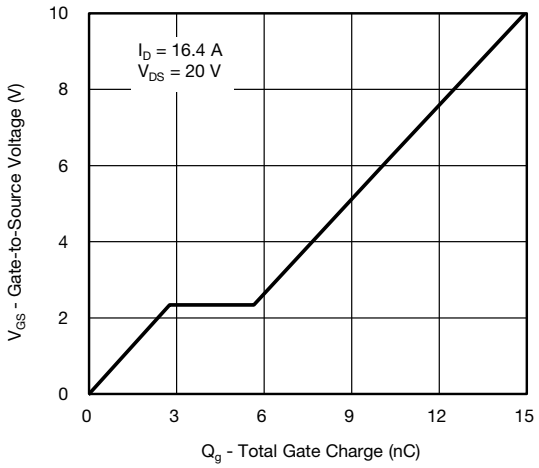


Transconductance

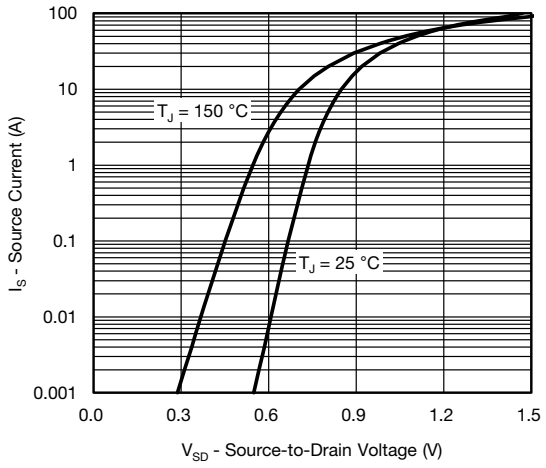


On-Resistance vs. Drain Current

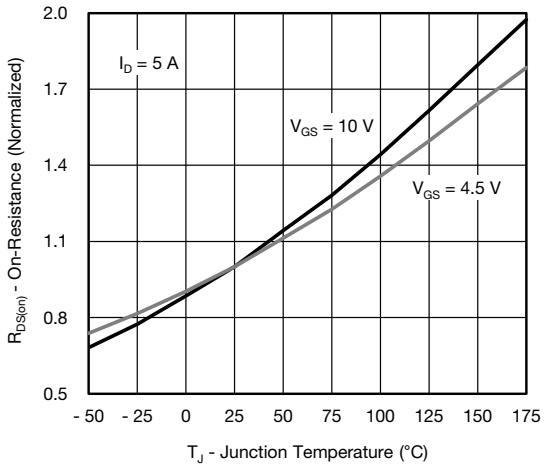
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



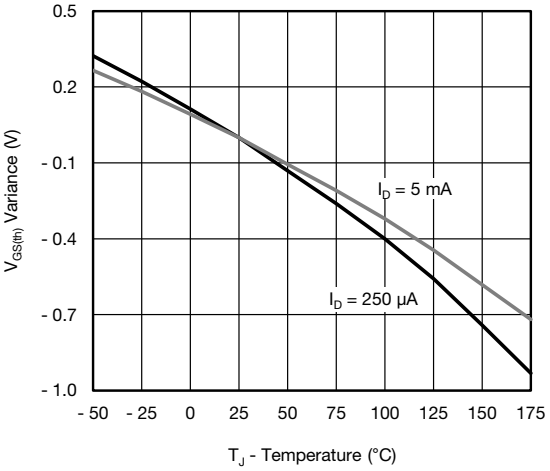
Gate Charge



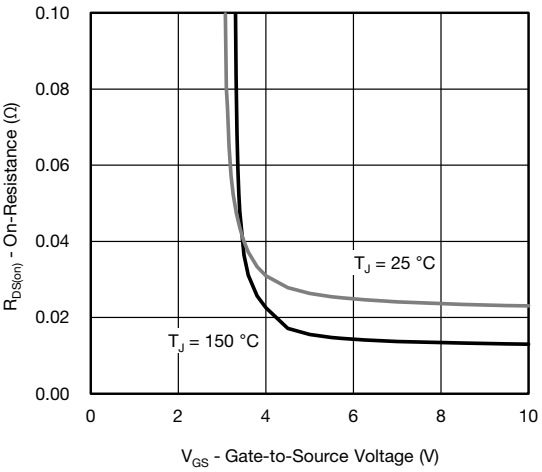
Source Drain Diode Forward Voltage



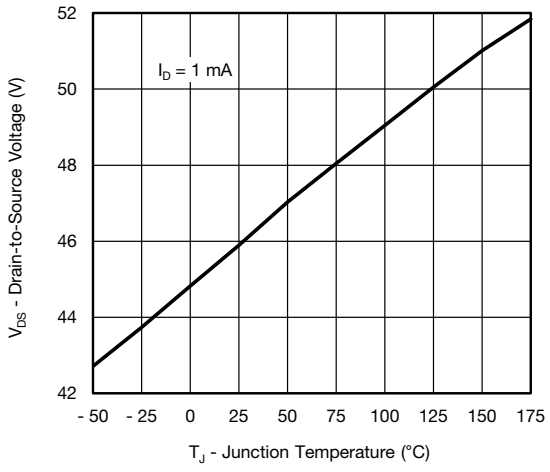
On-Resistance vs. Junction Temperature



Threshold Voltage

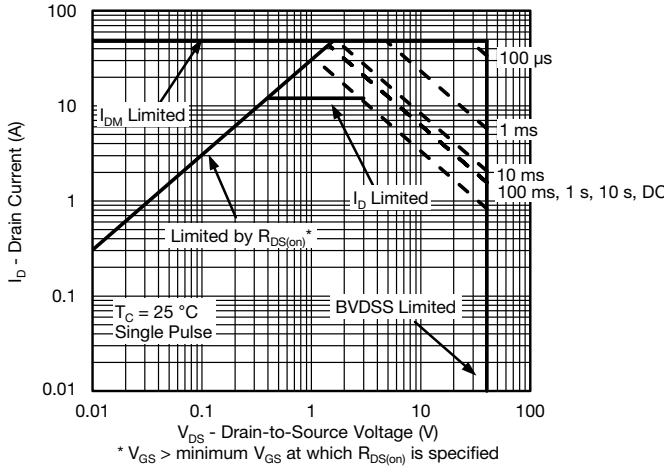


On-Resistance vs. Gate-to-Source Voltage

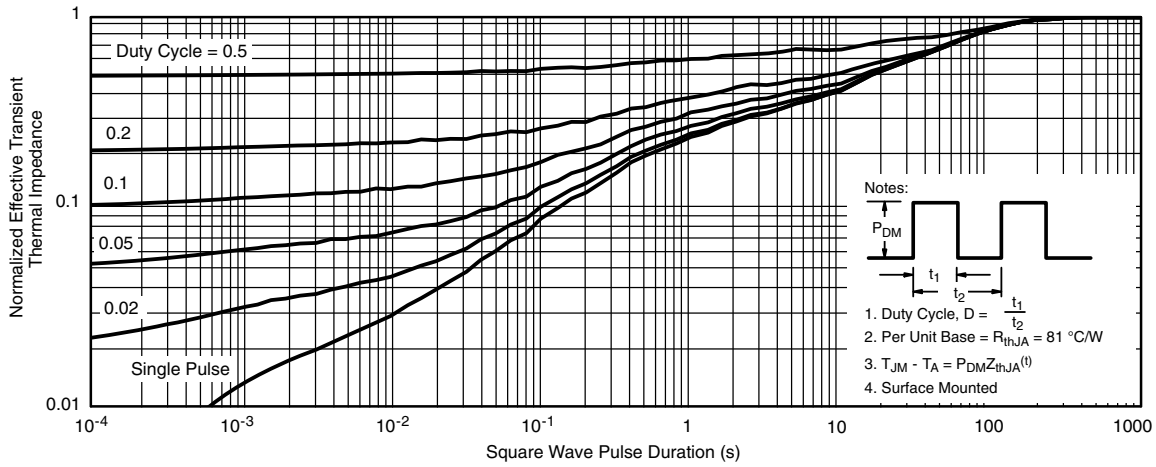


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

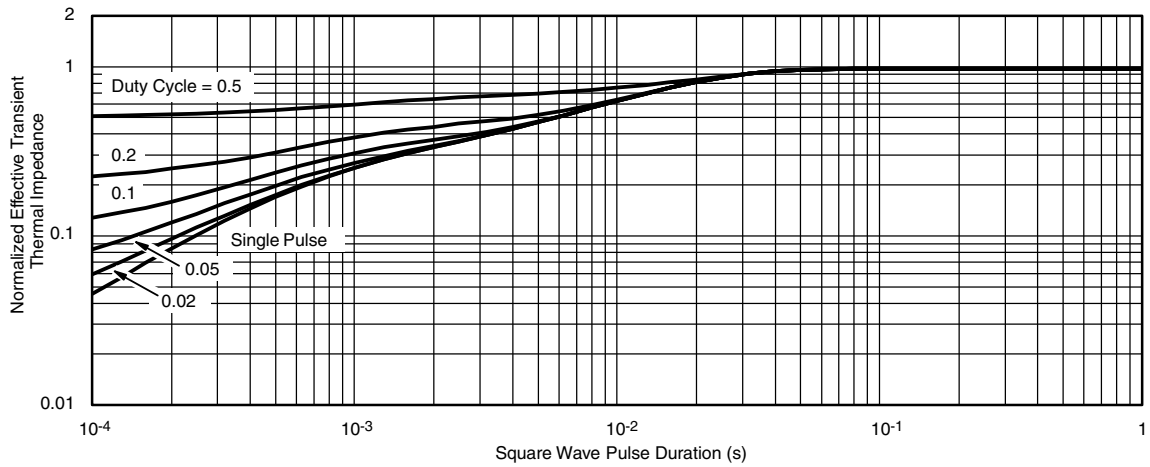


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62850.